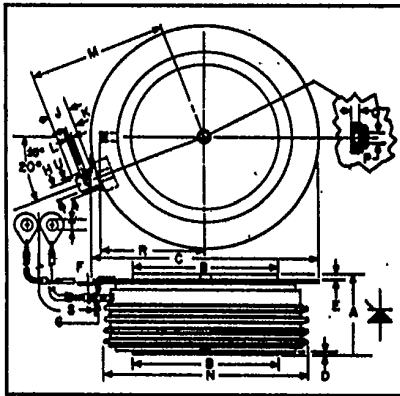
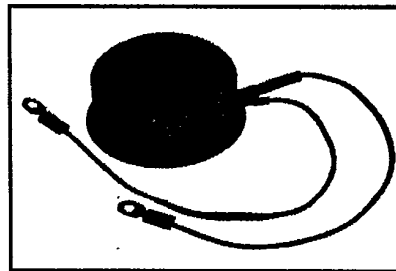


Phase Control SCR 1400-1500 Amperes Avg 500-1800 Volts



**C451
Outline Drawing**

Dimensions	Inches		Millimeters	
	Min.	Max.	Min.	Max.
A	1.020	1.065	25.90	27.05
B	1.845	1.855	46.86	47.12
C	—	2.940	—	74.68
D	.030	—	.76	—
E	.050	—	1.27	—
F	.017	.023	.43	.58
G	.057	.059	1.44	1.50
H	.186	.191	4.72	4.85
J	.245	.255	6.22	6.48
K	.115	.130	2.92	3.30
L	.064	.070	1.62	1.78
M	—	1.800	—	45.72
N	—	2.650	—	67.31
P	.135	.145	3.42	3.68
Q	.070	.100	1.77	2.54
R	—	1.355	—	34.42
S	12.219	12.343	310.36	313.51
T	.137	.153	3.47	3.89



**C451
Phase Control SCR
1400-1500 Amperes/500-1800 Volts**

Description

Powerex Silicon Controlled Rectifiers (SCR) are designed for phase control applications. These are all-diffused, Press-Pak (Pow-R-Disc) devices employing the field-proven amplifying (di/namic) gate.

Features:

- ☐ Low On-State Voltage
- ☐ High di/dt
- ☐ High dv/dt
- ☐ Hermetic Packaging
- ☐ Excellent Surge and P_t Ratings

Applications:

- ☐ Power Supplies
- ☐ Battery Chargers
- ☐ Motor Control
- ☐ Light Dimmers
- ☐ VAR Generators

Ordering Information

Example: Select the complete six or seven digit part number you desire from the table — i.e. C451M1 is a 600 Volt, 1500 Ampere Phase Control SCR.

Type	Voltage		Current	
	V _{RRM} V _{RRM}	Code	I _T (avg)	Code
C451	500	E	1500	1
	600	M	1400	2
	700	S		
	800	N		
	900	T		
	1000	P		
	1100	PA		
	1200	PB		
	1300	PC		
	1400	PD		
	1500	PE		
	1600	PM		
	1700	PS		
	1800	PN		

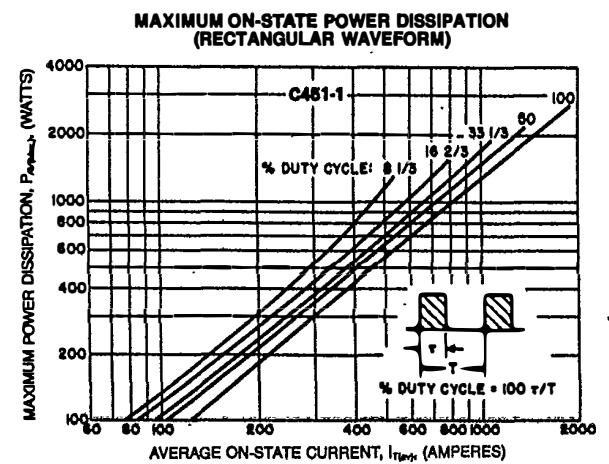
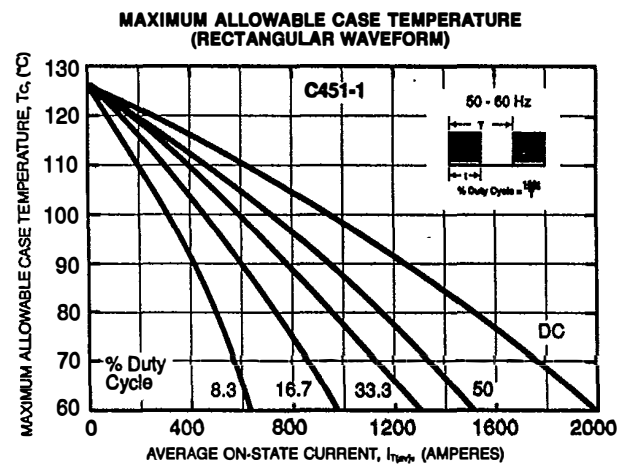
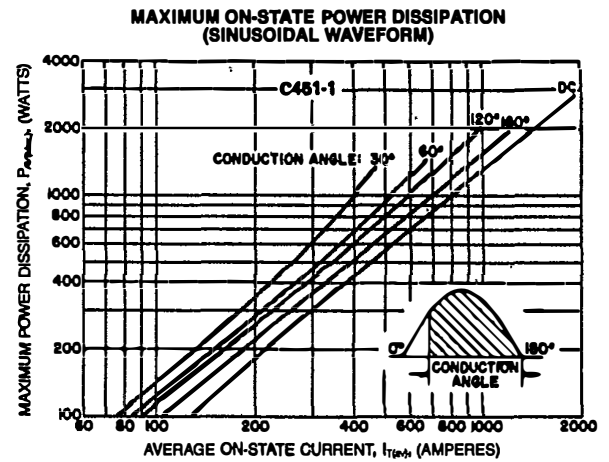
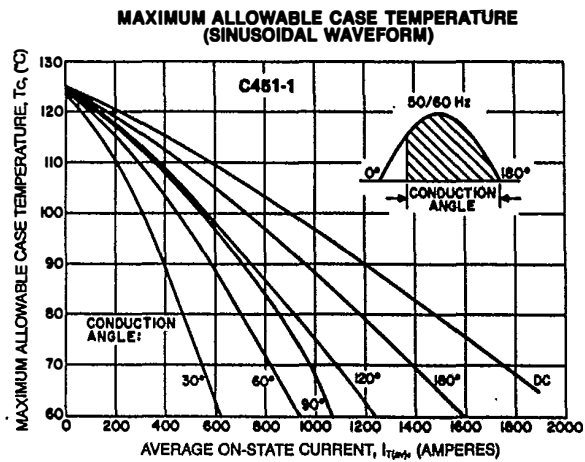
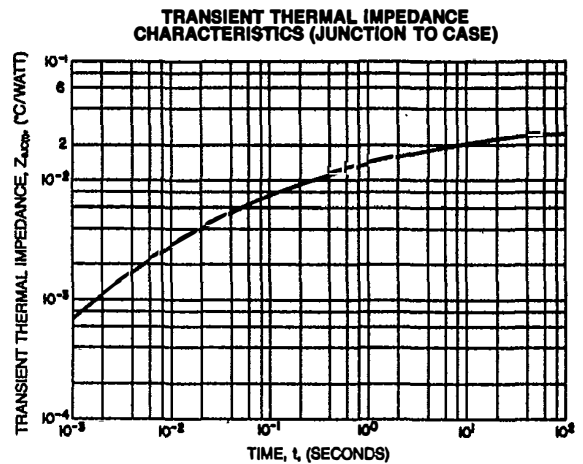
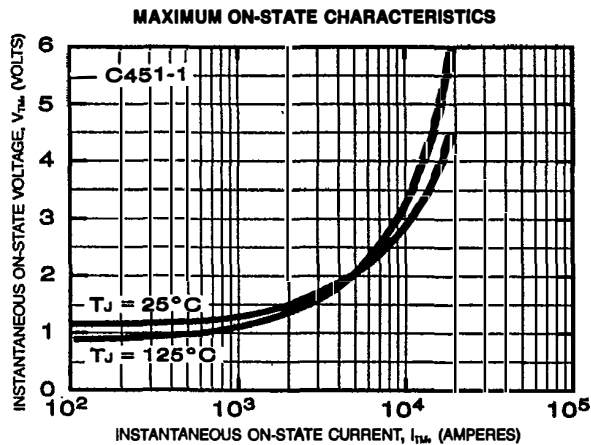
Absolute Maximum Ratings

	Symbol	C451-1	C451-2	Units
RMS On-State Current	$I_{T(RMS)}$	2350	2200	Amperes
Average On-State Current	$I_{T(av)}$	1500	1400	Amperes
Peak One-Cycle Surge (Non Repetitive) On-State Current (60Hz)	I_{TSM}	23,000	21,000	Amperes
Peak One-Cycle Surge (Non-Repetitive) On-State Current (50Hz)	I_{TSM}	20,800	19,200	Amperes
Critical Rate-of-Rise of On-State Current (Non-Repetitive)	di/dt	400	400	Amperes/ μs
Critical Rate-of-Rise of On-State Current (Repetitive)	di/dt	75	75	Amperes/ μs
I^2t (for Fusing), One Cycle at 60Hz	I^2t	2,200,000	1,830,000	A^2sec
Peak Gate Power Dissipation	P_{GM}	200	200	Watts
Average Gate Power Dissipation	$P_{G(av)}$	5	5	Watts
Storage Temperature	T_{STG}	-40 to 150	-40 to 150	$^{\circ}C$
Operating Temperature	T_J	-40 to 125	-40 to 125	$^{\circ}C$
Mounting Force ^①		5500 to 6000	5500 to 6000	lb.
Mounting Force ^①		24.5 to 26.7	24.5 to 26.7	kN

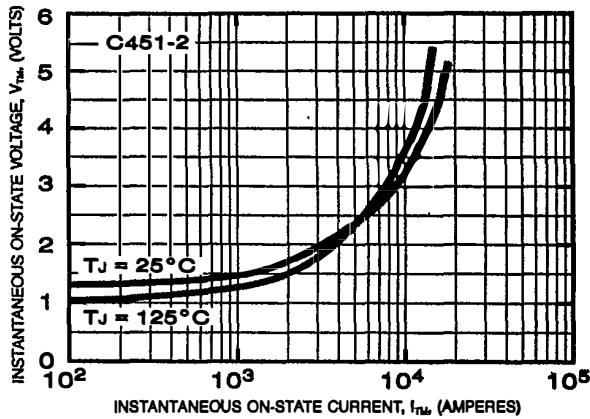
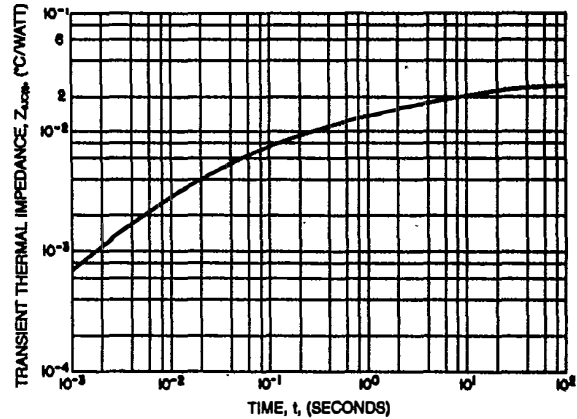
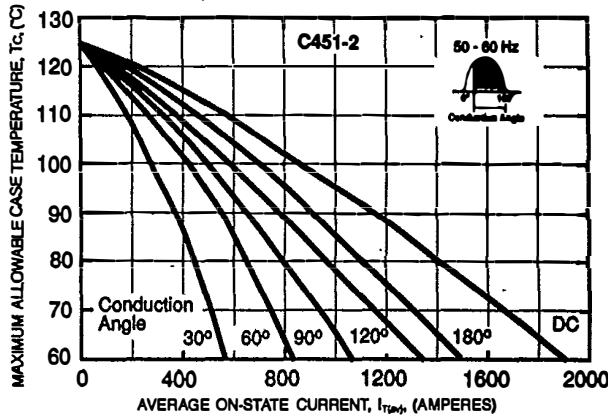
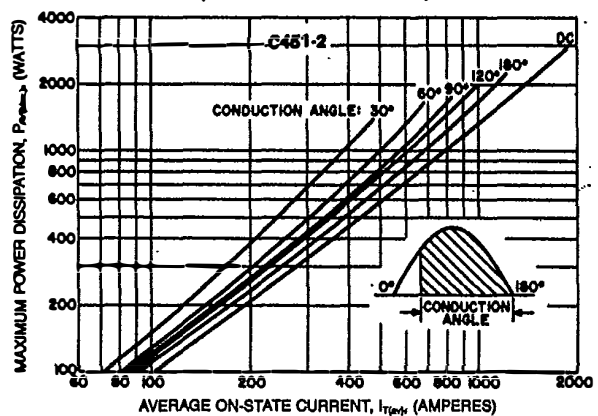
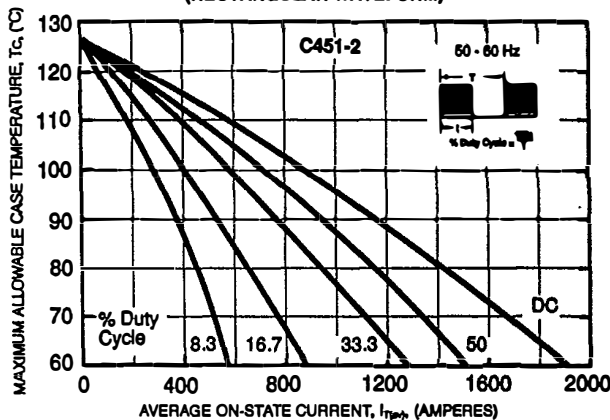
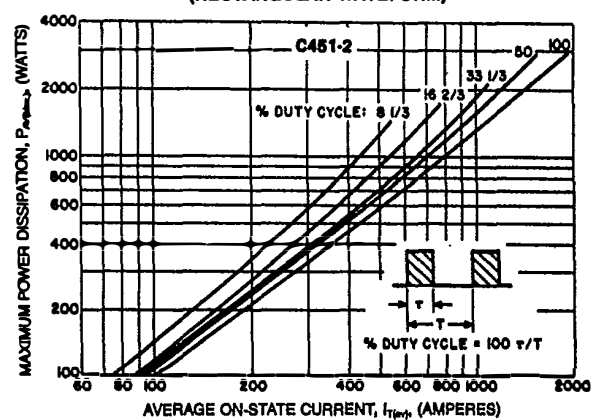
Electrical and Thermal Characteristics

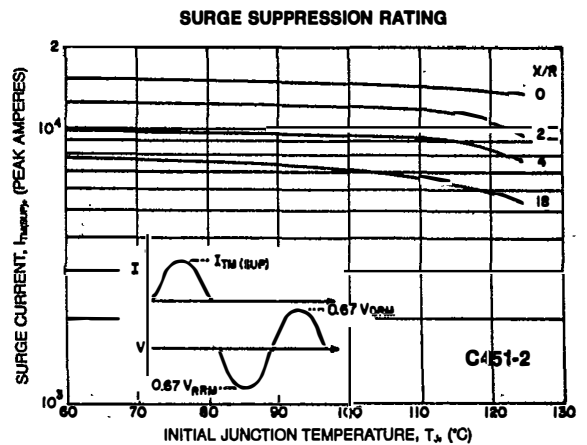
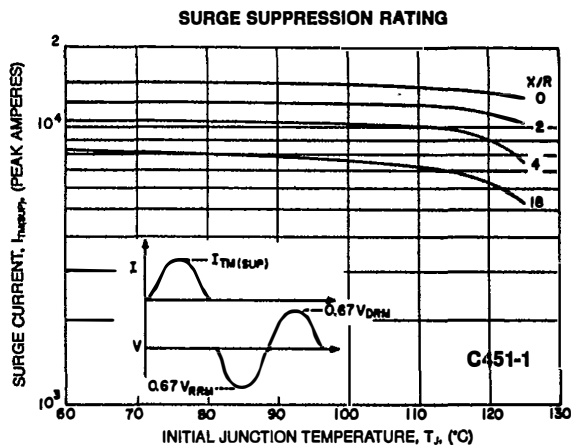
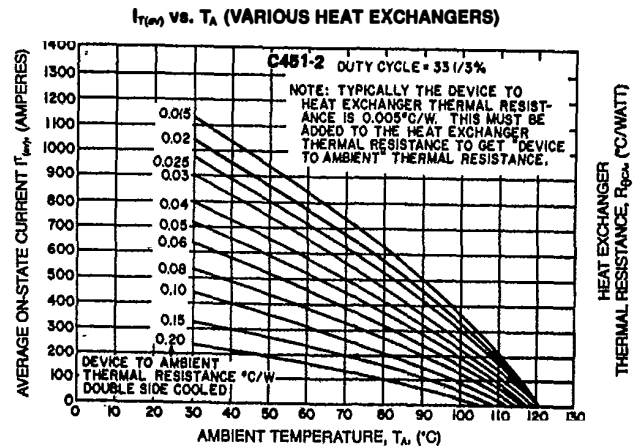
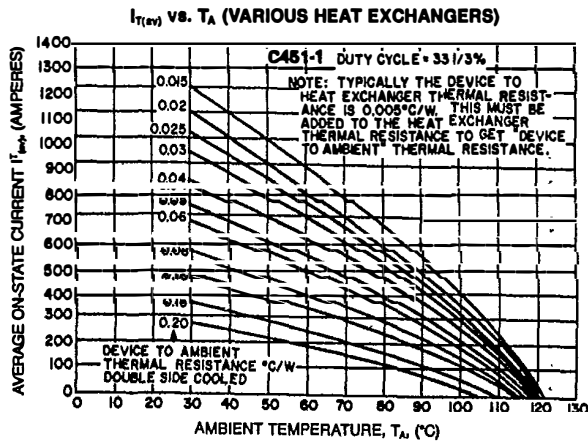
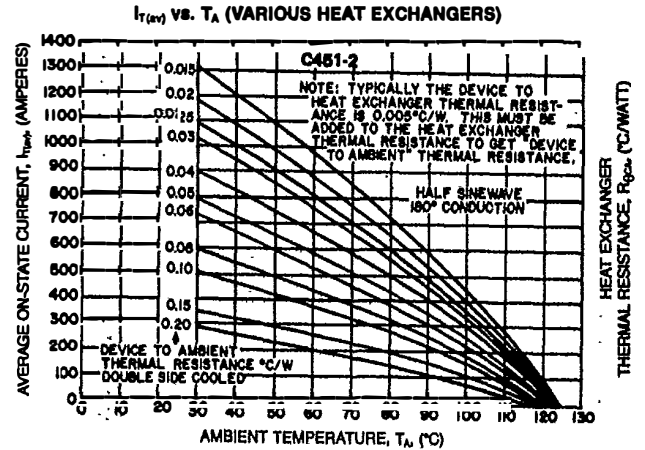
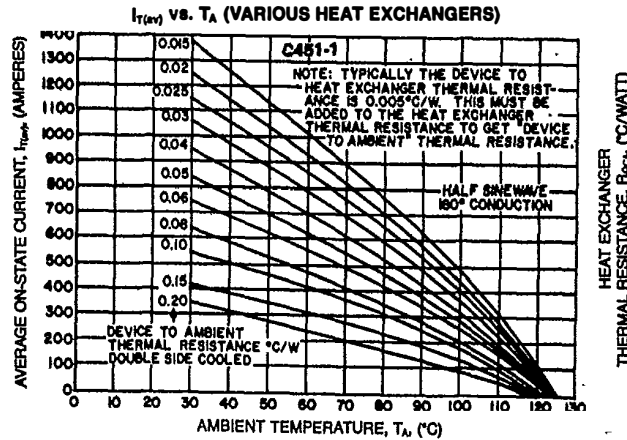
Characteristics	Symbol	Test Conditions	C451-1	C451-2	Units
Current—Conducting State Maximums					
Peak On-State Voltage	V_{TM}	$T_J = 25^{\circ}C$; $I_{TM} = 3000A$ Peak, Duty Cycle $\leq 0.01\%$	1.70	1.90	Volts
Voltage—Blocking State Maximums					
Forward Leakage, Peak	I_{DFM}	$T_J = 125^{\circ}C$, $V = V_{DFM}$	45		mA
Reverse Leakage, Peak	I_{RFM}	$T_J = 125^{\circ}C$, $V = V_{RFM}$	45		mA
Switching					
Typical Turn-Off Time	t_q	$T_J = 125^{\circ}C$, $I_T = 2000A$, Pulse Width = 1000 μsec ; $V_R = 50V$; $dv/dt = 200 V/\mu sec$; Linear to $.8 V_{DFM}$; $di_R/dt = 25A/\mu sec$; $V_G = 0$, $R_L = 100\Omega$	150		μsec
Typical Delay Time	t_d	$T_J = 25^{\circ}C$, $I_T = 50A$, Gate Supply = 20V; $R_L = 20\Omega$; Rise Time = 0.1/ μsec	.7		μsec
Min. Critical dv/dt exponential to V_{DFM}	dv/dt	$T_J = 125^{\circ}C$, 0.8 V_{DFM} Applied	400		V/ μsec
Thermal					
Maximum Thermal Resistance, ^① double sided cooling Junction to Case	$R_{\theta JC}$		.025		$^{\circ}C/Watt$
Case to Sink, Lubricated	$R_{\theta CS}$		.0075		$^{\circ}C/Watt$
Gate—Maximum Parameters					
Gate Current to Trigger	I_{GT}	$T_J = 25^{\circ}C$, $V_D = 20Vdc$, $R_L = 3\Omega$	200		mA
Gate Voltage to Trigger	V_{GT}	$T_J = -40$ to $125^{\circ}C$, $V_D = 20Vdc$, $R_L = 3\Omega$	5		Volts
Non-Triggering Gate Voltage	V_{GDM}	$V_D = \text{rated } V_{DFM}$, $T_J = 125^{\circ}C$, $R_L 1000\Omega$	.15		Volts
Peak Forward Gate Current	I_{GTM}		10		Amperes
Peak Reverse Gate Voltage	V_{GRM}		5		Volts

① Consult recommended mounting procedures.

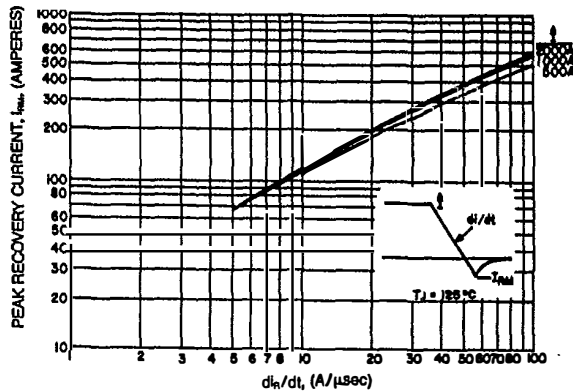


POWEREX

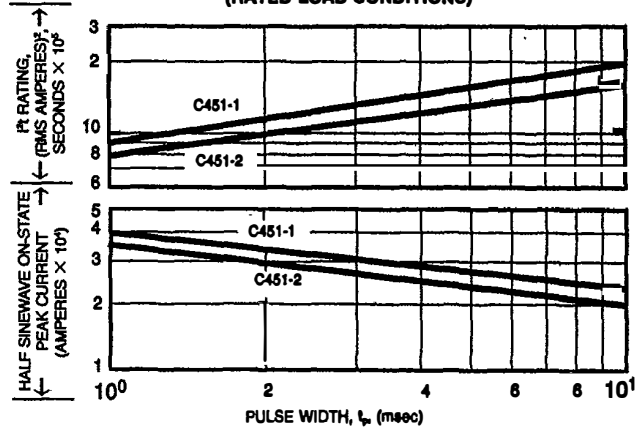
MAXIMUM ON-STATE CHARACTERISTICS

TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO CASE)

MAXIMUM ALLOWABLE CASE TEMPERATURE (SINUSOIDAL WAVEFORM)

MAXIMUM ON-STATE POWER DISSIPATION (SINUSOIDAL WAVEFORM)

MAXIMUM ALLOWABLE CASE TEMPERATURE (RECTANGULAR WAVEFORM)

MAXIMUM ON-STATE POWER DISSIPATION (RECTANGULAR WAVEFORM)




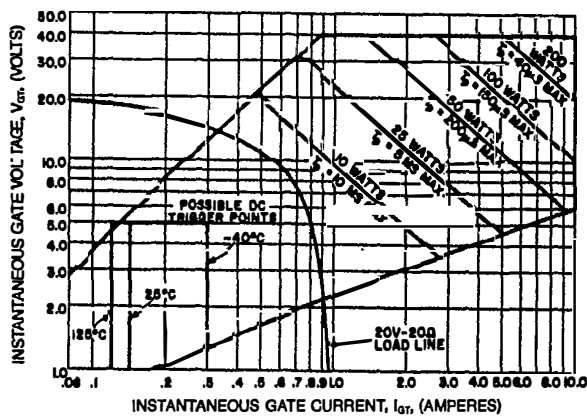
TYPICAL RECOVERY CURRENT



SUB-CYCLE SURGE AND P_T RATINGS
(RATED LOAD CONDITIONS)



GATE CHARACTERISTICS



NOTES:

1. Maximum allowable average gate dissipation = 5 watts.
2. The locus of possible dc trigger points lies outside the boundaries shown at various case temperatures.
3. T_p = rectangular gate current pulse width (5 μ s min. duration, 1 μ s max. rise time).
4. Maximum long-term, repetitive anode di/dt = 75 amps/ μ s with 20V-20 Ω gate source.